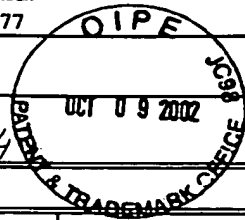


Form PTO 1449 U.S. Department of Commerce Patent and Trademark Office Information Disclosure Statement by Applicant	ATTY. DOCKET NUMBER NITT.0057	SERIAL NUMBER 10/031,377
	APPLICANT SUZUKI et al.	
	FILING DATE April 12, 2002	GROUP 2.674



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Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBC LASS	FILING DATE
KN	5,600,343	2/4/97	Sarrasin			4/27/95

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KN	62-8340	7/4/85	Japan				X
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Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

	International Search Report from Japanese Patent Office dated November 27, 2000
	OCT 15 2002
	Technology Center 2600

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Form PTO 1449 U.S. Department of Commerce Patent and Trademark Office Information Disclosure Statement by Applicant	ATTY. DOCKET NUMBER NITT.0057		SERIAL NUMBER Be Assigned
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	FILING DATE Concurrently Herewith	GROUP 2674	

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Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBC LASS	FILING DATE

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Examiner Initial		DOCUMENT NUMBER	FILING DATE	COUNTRY	CLAS s	SUB- CLASS	TRANSLATION	
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